TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

HN3C10FU

VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATIONS

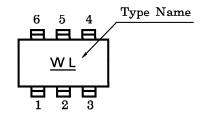
 Including Two Devices in US6 (Ultra Super Mini Type with 6 Leads)

MAXIMUM RATINGS (Ta = 25°C)

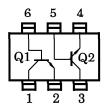
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	v_{CBO}	20	V
Collector-Emitter Voltage	V_{CEO}	12	V
Emitter-Base Voltage	V_{EBO}	3	V
Collector Current	$I_{\mathbf{C}}$	80	mA
Base Current	I _B	40	mA
Collector Power Dissipation	PC*	200	mW
Junction Temperature	T_{j}	125	°C
Storage Temperature Range	$T_{ m stg}$	-55~125	°C

*: Total

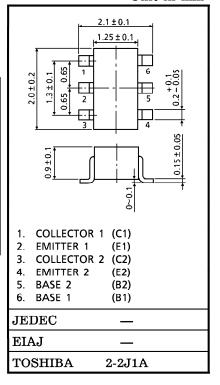
MARKING



PIN ASSIGNMENT (TOP VIEW)



Unit in mm



ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=10V, I_{E}=0$	_	_	1	μ A
Emitter Cut-off Current	$I_{ m EBO}$	$V_{EB}=1V, I_{C}=0$	_	-	1	μ A
DC Current Gain	$\mathbf{h_{FE}}$	$V_{CE} = 10V, I_{C} = 20mA$	80	_	240	_
Transition Frequency	${ m f_T}$	$V_{CE}=10V, I_{C}=20mA$	5	7	 	GHz
Insertion Gain	$ S_{21e} ^2$	$V_{CE} = 10V, I_{C} = 20mA, f = 1GHz$	8	11.5	_	dB
Noise Figure	NF	V_{CE} =10V, I_{C} =5mA, f=1GHz	_	1.1	2	dB
Reverse Transfer Capacitance Q1	$\mathrm{C_{re}}$	V _{CB} =10V, I _E =0, f=1MHz (Note)	_	0.7	1.2	pF
Reverse Transfer Capacitance Q2	$C_{\mathbf{re}}$		_	0.65	1.15	pF

(Note) Cre is measured by 3 terminal method capacitance bridge.

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